

**REMARKS**

Claims 1, 4, 6-9, 10, and 12 are pending in the application.

Claims 2, 3, 5, and 11 are canceled.

Claims 1, 4, 6, and 10 are currently amended.

No new matter is added.

Applicant requests reconsideration and allowance for the claims in light of the above amendments and following remark.

***Specification***

Following the Examiner's suggestion, the title of the invention is amended as follows.  
~~SEMICONDUCTOR DEVICE HAVING A CONTACT WINDOW AND FABRICATION~~

~~METHOD THEREOF~~

SEMICONDUCTOR DEVICE HAVING A CONTACT WINDOW INCLUDING A  
LOWER REGION WITH A WIDER WIDTH TO PROVIDE A LOWER CONTACT  
RESISTANCE

The first sentence of the specification (first paragraph, page 1) has been amended as required by the Examiner, to indicate that US Application Serial No. 10/341,766 is now US Patent No. 6,764,955.

The paragraph beginning on line 27, page 7 is amended as required by the Examiner.

***Claim Objections***

Claim 10 is objected to because of the following informality:

In claim 10, line 3, change "a upper" to —an upper—to correct grammar. In this regard, claim 10 is currently amended to make this change. Thus, applicant requests the objection be removed.

***Claim Rejection – 35 USC § 112***

Claims 2-3 are rejected under 35 U.S.C. § 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention. Claims 2-3 are canceled, rendering this rejection moot. However, the elements of claims 2-3 are written into currently amended claim 1, and, in this regard, the problem of insufficient antecedent basis is corrected.

***Claim Rejections – 35 USC § 102***

Claims 1-11 are rejected under 35 U.S.C. § 102(b) as being anticipated by IBM Technical Disclosure Bulletin, Vol. 35, no. 2, pp. 51-53, July 1992 ("IBM").

Applicant respectfully traverses the rejections.

Claim 1 is currently amended to recite,

"...a plurality of conductive patterns disposed between the lower dielectric layer and the upper dielectric layer, wherein the conductive patterns are spaced apart from the contact window a plurality of conductive patterns disposed between the lower dielectric layer and the upper dielectric layer, wherein the conductive patterns are *spaced apart* from the contact window..." (emphasis added). The Specification at page 9, lines 23-24 of the present application states "...it is possible to maximize the exposed area of the impurity active region 203 *without exposing the conductive patterns* 207 and improve the contact resistance..." (emphasis added). Therefore the conductive patterns are "spaced apart" from the contact window 219', which has a width 221' (Fig. 8, page 9, lines 6-8), so the conductive patterns 207 are not exposed to the contact window 219'.

On the contrary, IBM clearly shows, in Fig. 1(b), the p-implanted polysilicon (i.e. the conductive pattern) making contact with the undercut emitter window (i.e. the contact window). As further evidence of this contact, the text reads "The cpi (cpitaxial base) will link up self-aligned to the p-poly extrinsic base contact underneath the spacer (Fig. 1c)."

Thus, IBM does not teach the above limitations of claim 1 and does not therefore anticipate claim 1, and applicant requests reconsideration of allowability of claim 1.

Claims 2 and 3 are canceled.

Claim 4 is currently amended to recite,

"a plurality of conductive patterns in the dielectric layer, wherein the plurality of conductive patterns is *spaced apart* from the contact window" (emphasis added). As discussed above with regarding claim 1, IBM does not teach or disclose the above limitations of claim 4. Thus, IBM does not anticipate claim 4, and applicant requests reconsideration of allowability of claim 4.

Claim 5 is canceled.

Claims 6-9 recite additional novel and non-obvious features of their base claim 4. Therefore allowance of claims 6-9 is requested.

Claim 10 is currently amended to recite,

"a plurality of conductive patterns intervening between the second dielectric layer and the upper dielectric layer, wherein the conductive patterns are *spaced apart* from the contact window" (emphasis added). For the reasons discussed above with respect to claim 1, IBM does not anticipate claim 10, and applicant requests reconsideration of allowability of claim 10.

Claim 11 is canceled.

Claim 12 recites additional novel and non-obvious features of its base claim 10.

Therefore allowance of claim 12 is requested.

Claims 1, 2, 10, 12, are rejected under 35 U.S.C. § 102(b) as being anticipated by Sakaemori, JP 10-270555 A, ("Sakaemori") using US 6,740,584 B2 as an English equivalent translation.

Applicant respectfully traverses the rejections.

Claim 1 is currently amended to include all of the limitations of original claim 3, which is not anticipated by Sakaemori (and which the Examiner did not reject in view of Sakaemori). Therefore, allowance of currently amended claim 1 is requested.

Claim 2 is canceled, rendering the rejection moot.

Claim 10 is currently amended to include all of the limitations of original claim 11, which is not anticipated by Sakaemori (and which the Examiner did not reject in view of Sakaemori). Therefore, allowance of currently amended claim 10 is requested.

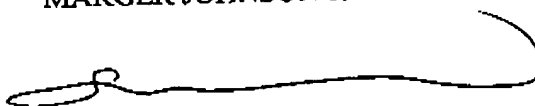
Claim 12 recites additional novel and non-obvious features of its base claim 10. Therefore allowance of claim 12 is requested

For the foregoing reasons, reconsideration and allowance of claims 1, 4, 6-9, 10, and 12 of the application as amended is solicited. The Examiner is encouraged to telephone the undersigned at (503) 222-3613 if it appears that an interview would be helpful in advancing the case.

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Respectfully submitted,

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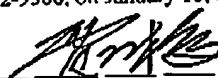


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Limited Recognition Under 37 CFR § 10.9(b)

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I hereby certify that this correspondence  
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